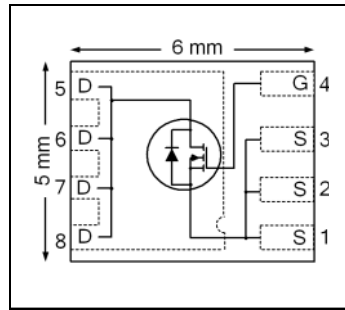


V_{DS}	40	V
$R_{DS(on) \max}$	2.6	mΩ
Q_g (typical)	73	nC
R_G (typical)	1.2	Ω
I_D (@ $T_{mb} = 25^\circ\text{C}$)	188Ⓞ	A



Applications

- Secondary Side Synchronous Rectification
- Inverter for DC Motors
- DC-DC Brick Application
- Boost Converters

Features

Low $R_{DS(ON)}$ ($\leq 2.6 \text{ m}\Omega$)
Low Thermal Resistance to PCB ($<0.8^\circ\text{C/W}$)
100% R_g Tested
Low Profile ($\leq 0.9 \text{ mm}$)
Industry-Standard Pinout
Compatible with Existing Surface Mount Techniques
RoHS Compliant, Halogen-Free
MSL1, Industrial Qualification

results in
⇒

Benefits

Lower Conduction Losses
Enable better Thermal Dissipation
Increased Reliability
Increased Power Density
Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFH5004PbF	PQFN 5 mm x 6 mm	Tape and Reel	4000	IRFH5004TRPbF

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	40	V
V_{GS}	Gate-to-Source Voltage	± 20	
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	28	A
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	23	
$I_D @ T_{mb} = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	188Ⓞ	
$I_D @ T_{mb} = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	119Ⓞ	
I_{DM}	Pulsed Drain Current①	752	
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation⑤	3.6	W
$P_D @ T_{mb} = 25^\circ\text{C}$	Power Dissipation⑤	156	
	Linear Derating Factor⑤	0.029	W/°C
T_J	Operating Junction and	-55 to + 150	°C
T_{STG}	Storage Temperature Range		

Notes ① through ⑦ are on page 9

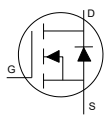
Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	40	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.04	—	V/°C	Reference to 25°C, I _D = 1.0mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	2.1	2.6	mΩ	V _{GS} = 10V, I _D = 50A ②
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 150μA
ΔV _{GS(th)}	Gate Threshold Voltage Coefficient	—	-5.6	—	mV/°C	
I _{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	V _{DS} = 40V, V _{GS} = 0V
		—	—	250		V _{DS} = 40V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20 V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20 V
g _{fs}	Forward Transconductance	91	—	—	S	V _{DS} = 15 V, I _D = 50A
Q _g	Total Gate Charge	—	73	110	nC	V _{DS} = 20V I _D = 50A V _{GS} = 4.5V See Fig.17 & 18
Q _{gs1}	Pre-V _{th} Gate-to-Source Charge	—	15	—		
Q _{gs2}	Post-V _{th} Gate-to-Source Charge	—	6.1	—		
Q _{gd}	Gate-to-Drain Charge	—	27	—		
Q _{godr}	Gate Charge Overdrive	—	25	—		
Q _{sw}	Switch Charge (Q _{gs2} + Q _{gd})	—	33.1	—		
Q _{oss}	Output Charge	—	27	—	nC	V _{DS} = 16V, V _{GS} = 0V
R _G	Gate Resistance	—	1.2	—	Ω	
t _{d(on)}	Turn-On Delay Time	—	13	—	ns	V _{DD} = 20V, V _{GS} = 10V I _D = 50A R _G = 1.8Ω
t _r	Rise Time	—	39	—		
t _{d(off)}	Turn-Off Delay Time	—	28	—		
t _f	Fall Time	—	16	—		
C _{iss}	Input Capacitance	—	4490	—	pF	V _{GS} = 0V V _{DS} = 20V f = 1.0MHz
C _{oss}	Output Capacitance	—	970	—		
C _{rss}	Reverse Transfer Capacitance	—	460	—		

Avalanche Characteristics

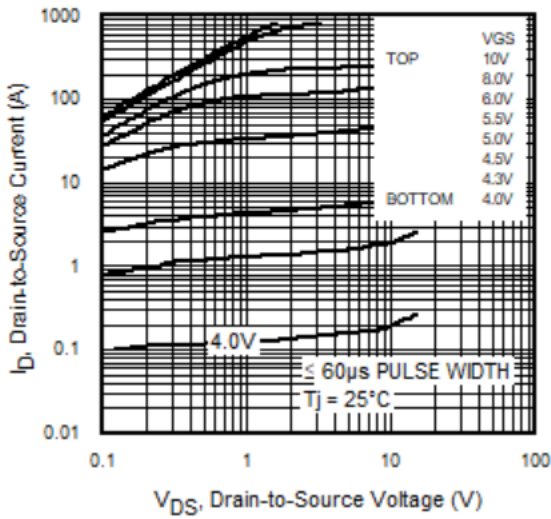
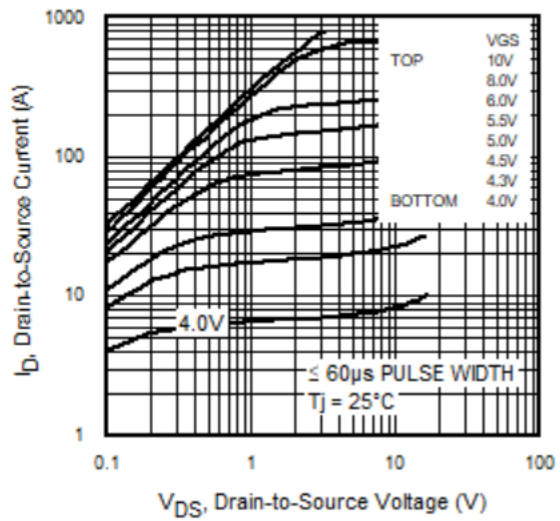
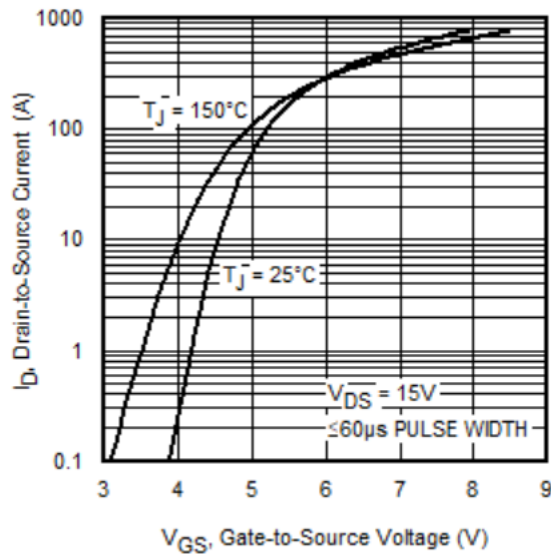
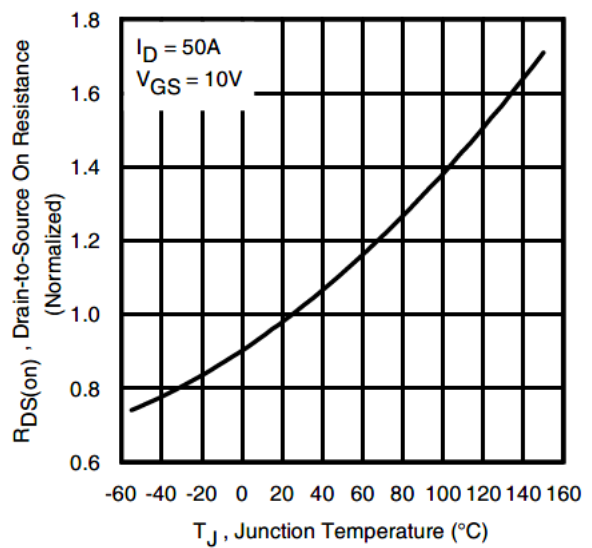
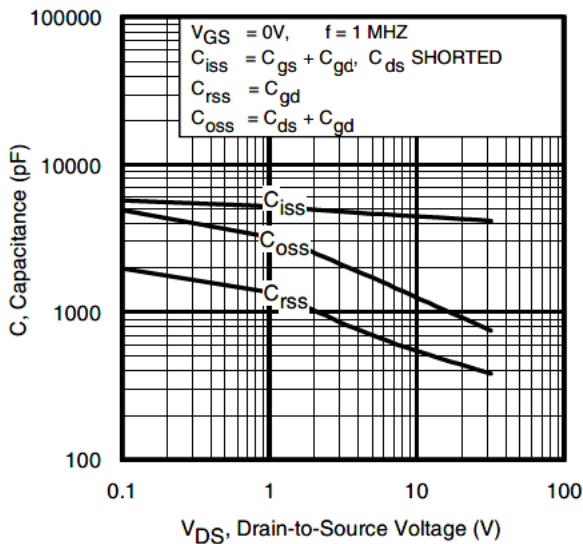
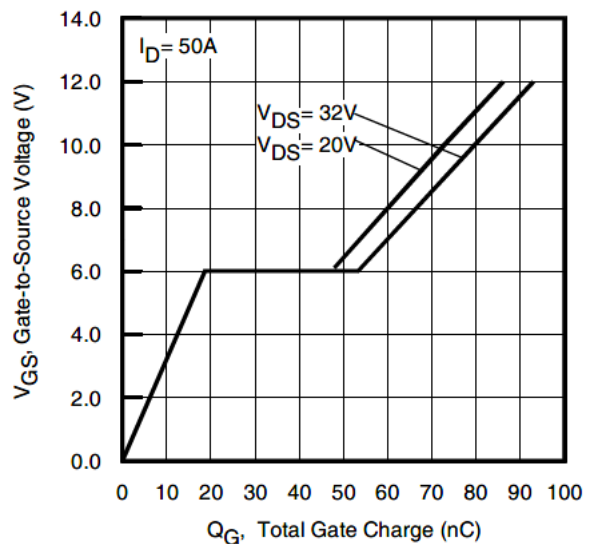
	Parameter	Typ.	Max.	Units
E _{AS}	Single Pulse Avalanche Energy ②	—	340	mJ
I _{AR}	Avalanche Current①	—	50	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	156	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode)	—	—	752①		
V _{SD}	Diode Forward Voltage	—	—	1.0	V	T _J = 25°C, I _S = 50A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	—	32	48	ns	T _J = 25°C, I _F = 50A, V _{DD} = 20V
Q _{rr}	Reverse Recovery Charge	—	100	150	nC	di/dt = 300A/μs ③

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC} (Bottom)	Junction-to-Mounting Base	—	0.8	°C/W
R _{θJC} (Top)	Junction-to-Case ④	—	15	
R _{θJA}	Junction-to-Ambient ⑤	—	35	
R _{θJA} (<10s)	Junction-to-Ambient ⑤	—	33	


Fig 1. Typical Output Characteristics

Fig 2. Typical Output Characteristics

Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance vs. Temperature

Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

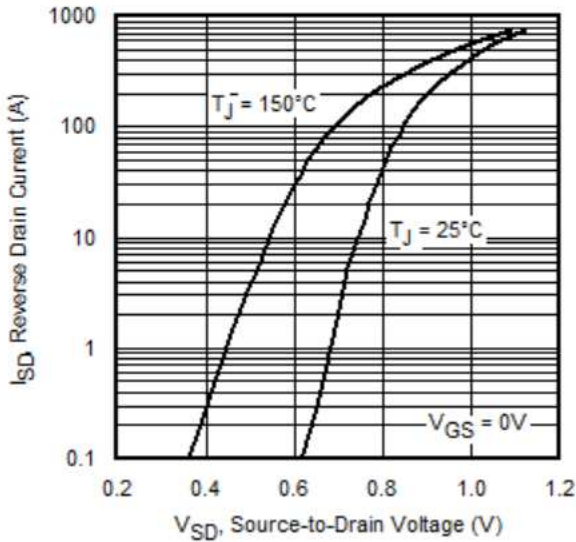


Fig 7. Typical Source-Drain Diode Forward Voltage

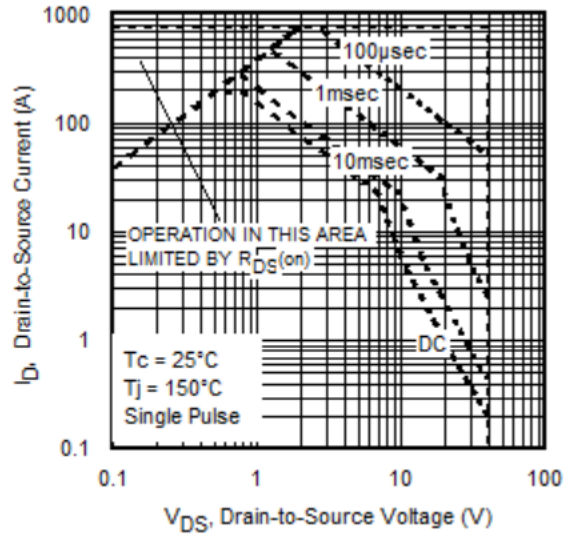


Fig 8. Maximum Safe Operating Area

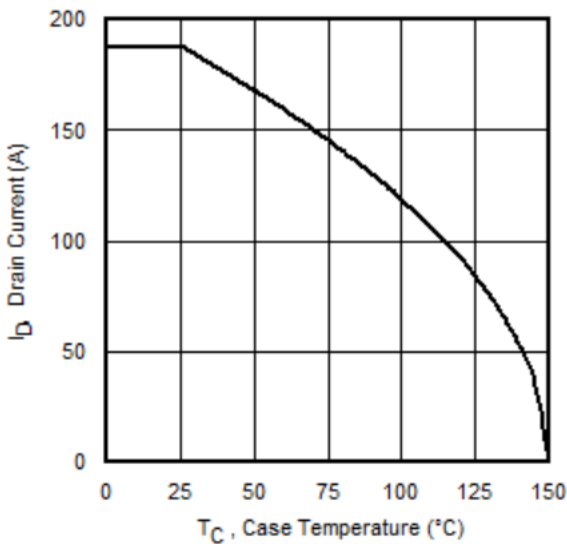


Fig 9. Maximum Drain Current vs. Case Temperature

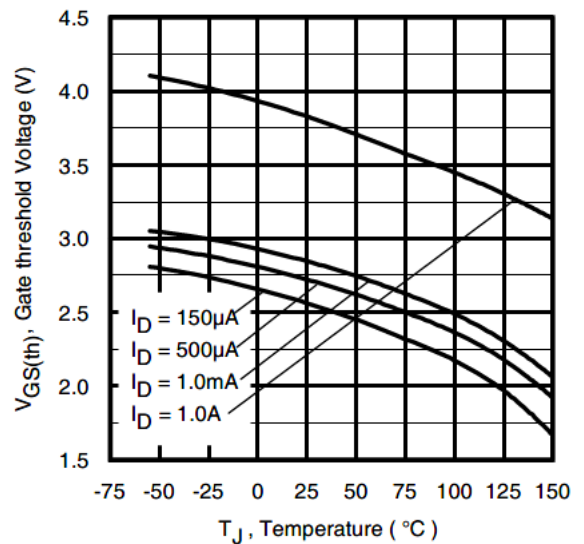


Fig 10. Drain-to-Source Breakdown Voltage

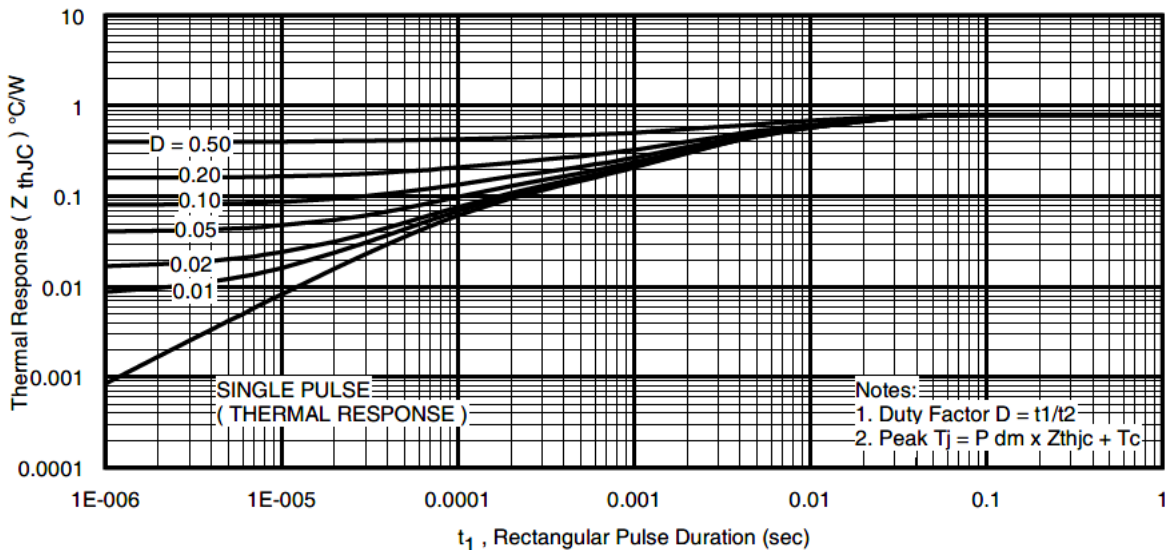


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-

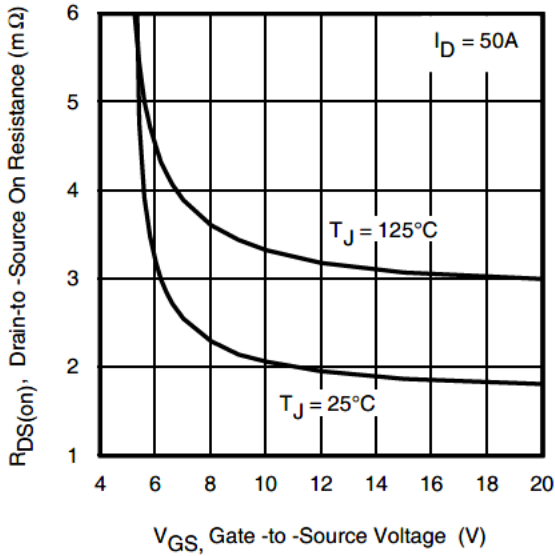


Fig 12. On-Resistance vs. Gate Voltage

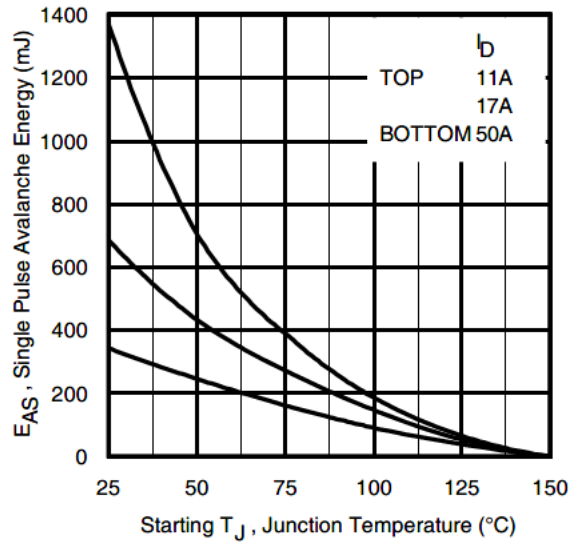


Fig 13. Maximum Avalanche Energy vs. Drain Current

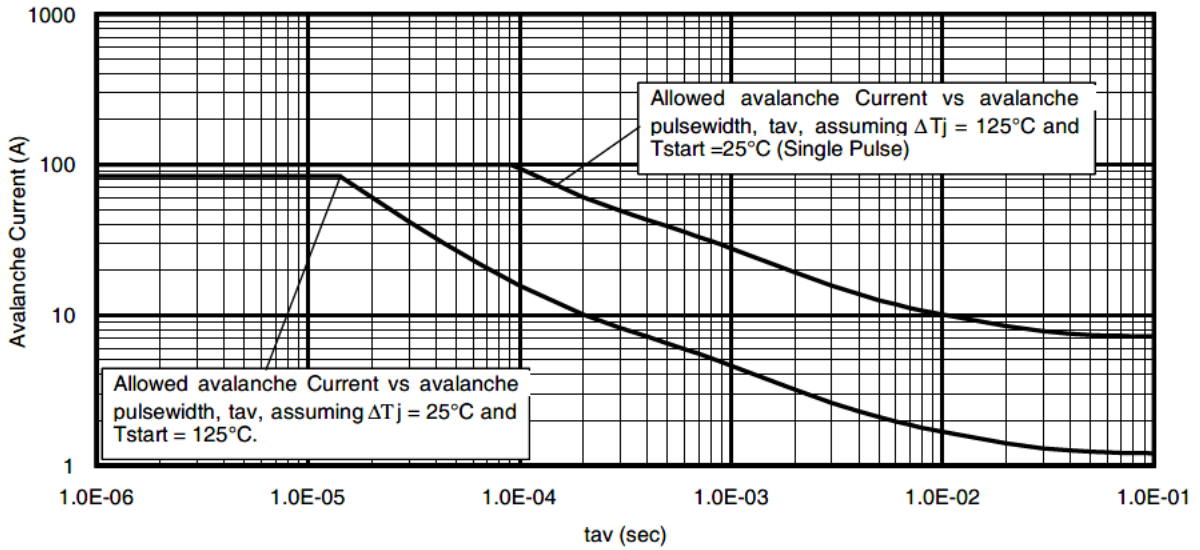
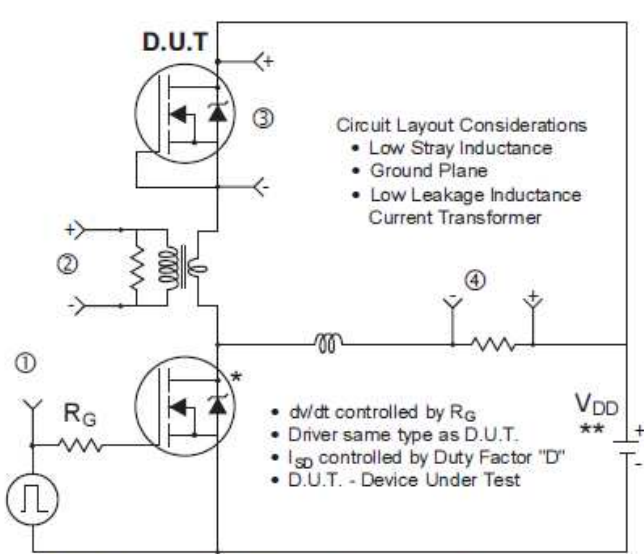
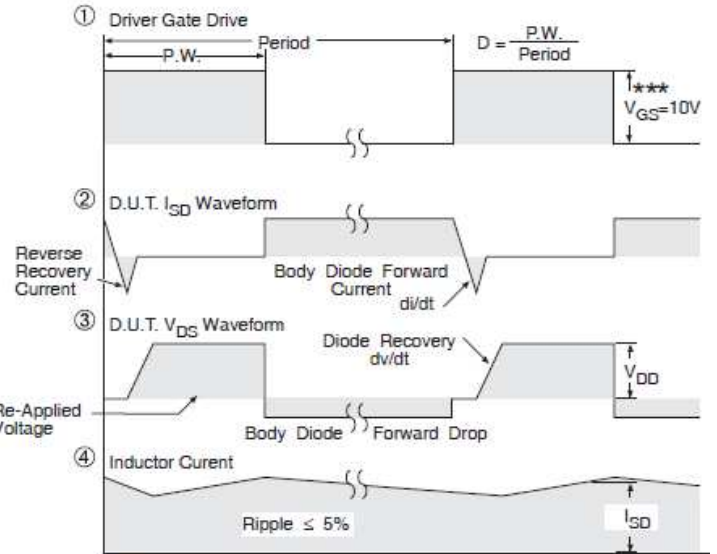


Fig 14. Single Avalanche Event: Pulse Current vs. Pulse Width



* Use P-Channel Driver for P-Channel Measurements
 ** Reverse Polarity for P-Channel



*** $V_{GS} = 5V$ for Logic Level Devices

Fig 15. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET[®] Power MOSFETs

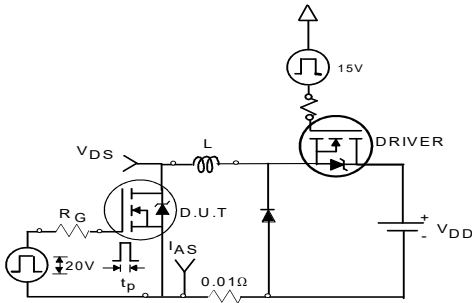


Fig 16a. Unclamped Inductive Test Circuit

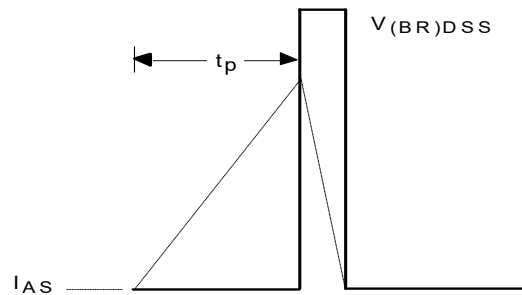


Fig 16b. Unclamped Inductive Waveforms

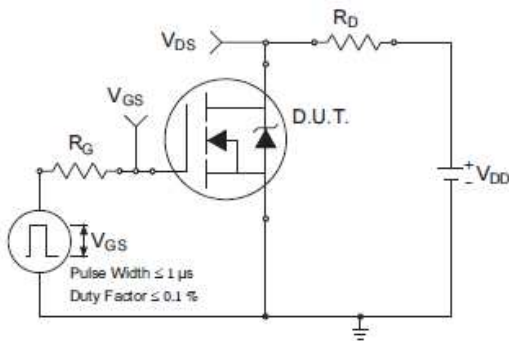


Fig 17a. Switching Time Test Circuit

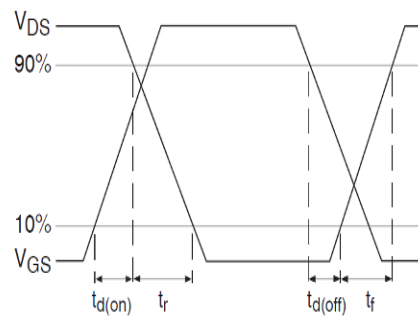


Fig 17b. Switching Time Waveforms

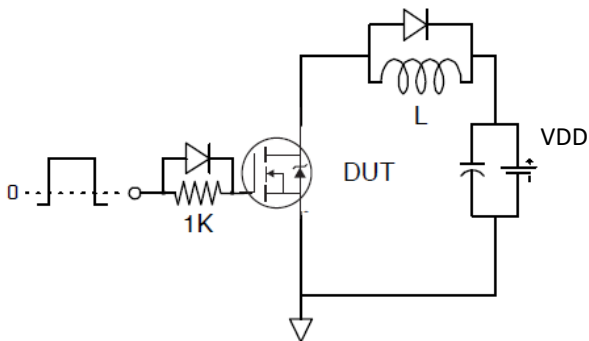


Fig 18. Gate Charge Test Circuit

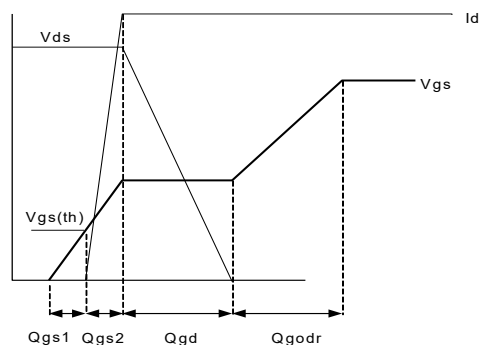
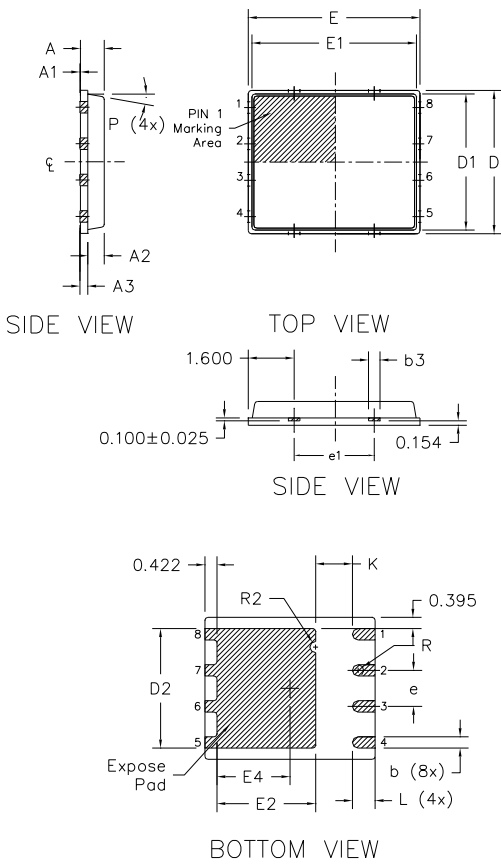


Fig 19. Gate Charge Waveform

PQFN 5x6 Outline "B" Package Details



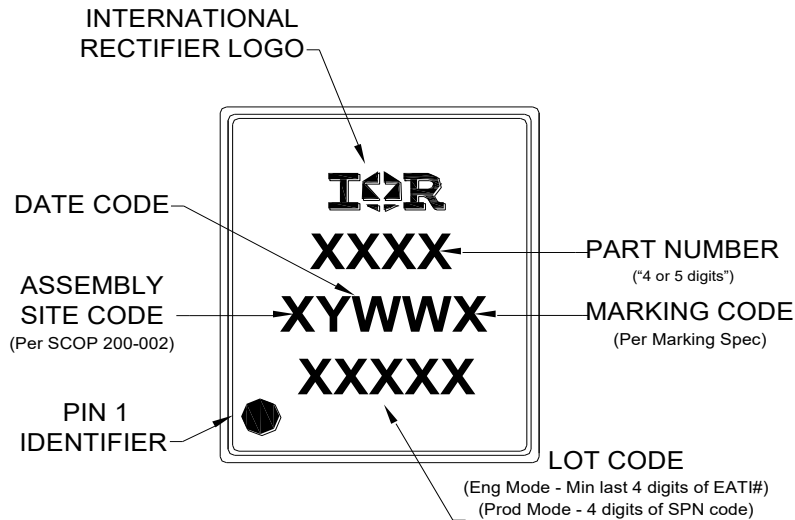
DIM SYMBOL	MILLIMETERS		INCH	
	MIN	MAX	MIN	MAX
A	0.800	0.900	0.0315	0.0543
A1	0.000	0.050	0.0000	0.0020
A3	0.200 REF		0.0079 REF	
b	0.350	0.470	0.0138	0.0185
b1	0.025	0.125	0.0010	0.0049
b2	0.210	0.410	0.0083	0.0161
b3	0.150	0.450	0.0059	0.0177
D	5.000 BSC		0.1969 BSC	
D1	4.750 BSC		0.1870 BSC	
D2	4.100	4.300	0.1614	0.1693
E	6.000 BSC		0.2362 BSC	
E1	5.750 BSC		0.2264 BSC	
E2	3.380	3.780	0.1331	0.1488
e	1.270 REF		0.0500 REF	
e1	2.800 REF		0.1102 REF	
K	1.200	1.420	0.0472	0.0559
L	0.710	0.900	0.0280	0.0354
P	0°	12°	0°	12°
R	0.200 REF		0.0079 REF	
R2	0.150	0.200	0.0059	0.0079

Note:

1. Dimensions and tolerancing confirm to ASME Y14.5M-1994
2. Dimension L represents terminal full back from package edge up to 0.1mm is acceptable
3. Coplanarity applies to the expose Heat Slug as well as the terminal
4. Radius on terminal is Optional

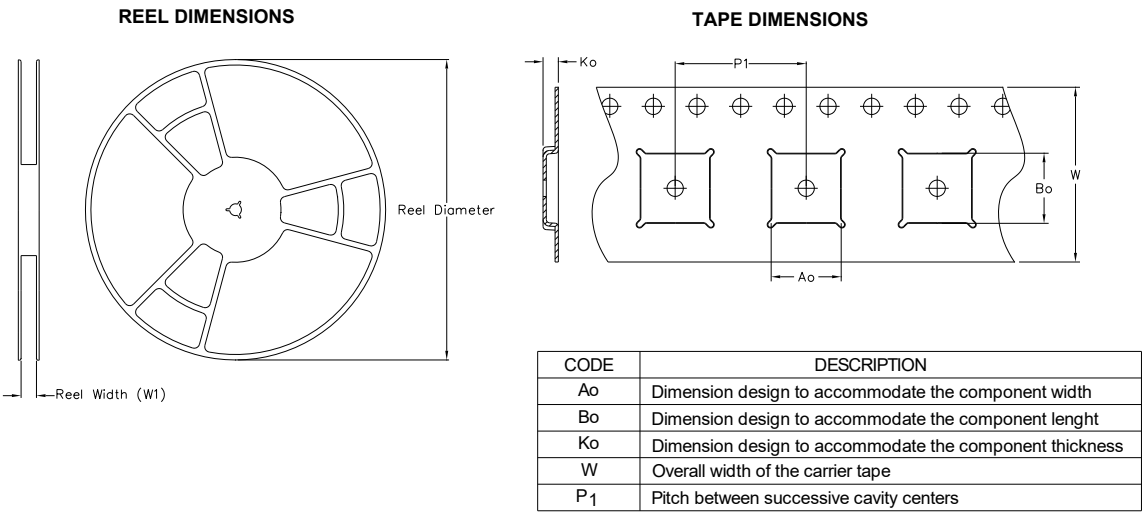
For more information on board mounting, including footprint and stencil recommendation, please refer to application note AN-1136: <http://www.irf.com/technical-info/appnotes/an-1136.pdf>
 For more information on package inspection techniques, please refer to application note AN-1154: <http://www.irf.com/technical-info/appnotes/an-1154.pdf>

PQFN 5x6 Part Marking

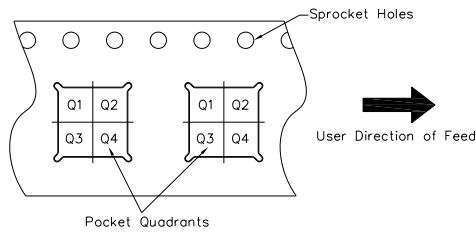


Note: For the most current drawing please refer to IR website at <http://www.irf.com/packaging>

PQFN 5x6 Tape and Reel



QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Note: All dimension are nominal

Package Type	Reel Diameter (Inch)	QTY	Reel Width W1 (mm)	Ao (mm)	Bo (mm)	Ko (mm)	P1 (mm)	W (mm)	Pin 1 Quadrant
5 X 6 PQFN	13	4000	12.4	6.300	5.300	1.20	8.00	12	Q1

Note: For the most current drawing please refer to IR website at <http://www.irf.com/packaging>

Qualification Information

Qualification Level	Industrial (per JEDEC JESD47F [†] guidelines)	
Moisture Sensitivity Level	PQFN 5mm x 6mm	MSL1 (per JEDEC J-STD-020D [†])
RoHS Compliant	Yes	

† Applicable version of JEDEC standard at the time of product release.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 0.27\text{mH}$, $R_G = 50\Omega$, $I_{AS} = 50\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ R_θ is measured at T_J of approximately 90°C .
- ⑤ When mounted on 1 inch square 2 oz copper pad on 1.5x1.5 in. board of FR-4 material
- ⑥ Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 9. De-rating will be required based on the actual environmental conditions.

Revision History

Date	Rev.	Comments
01/13/2014	2.1	<ul style="list-style-type: none"> • Updated ordering information to reflect the End-of-Life (EOL) of the mini-reel option (EOL notice #259) • Updated data sheet with the new IR corporate template.
04/28/2015	2.2	<ul style="list-style-type: none"> • Updated package outline for "option B" and added package outline for "option G" on page 7 • Updated tape and reel on page 8.
5/19/2015	2.3	<ul style="list-style-type: none"> • Updated package outline for "option G" on page 7 • Updated "IFX logo" on page 1 and page 9
12/08/2020	2.4	<ul style="list-style-type: none"> • Updated datasheet based on IFX template. • Updated Datasheet based on new current rating and application note :App-AN_1912_PL51_2001_180356

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